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AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A multilayer thin film formed on ~~an~~ a Si substrate by epitaxial growth, the multilayer thin film comprising:

a buffer layer formed on said Si substrate, where said buffer layer includes

- an oxide thin film of zirconium or of a rare earth element on said Si substrate;
- ~~a first perovskite oxide thin film on said oxide thin film;~~ and
- an electrically conductive thin film having (100) or (001) orientation on said ~~first perovskite oxide thin film,~~

a ~~second~~ perovskite oxide thin film formed on said buffer layer, which is grown epitaxially with respect to said buffer layer, ~~where said second perovskite oxide thin film comprises PbTiO₃ and has a (100) or (001) orientation, and~~

a ferroelectric thin film having (100) and (001) orientation, which has a different composition than ~~the second~~ said perovskite oxide thin film and which is epitaxially grown on said ~~second~~ perovskite oxide thin film.

Claim 2 (Previously Presented): The multilayer thin film of claim 1, wherein said second perovskite oxide thin film has insulating properties.

Claims 3-4 (Canceled)

Claim 5 (Previously Presented): The multilayer thin film of claim 1, wherein said ferroelectric thin film comprises PZT.